Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!

Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832
Email & Skype: info@chipsmall.com Web: www.chipsmall.com
Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China

Ordering number : ENA1184A

ECH8663R

N-Channel Power MOSFET
30V, 8A, 20.5mΩ, Dual ECH8

ON Semiconductor®
http://onsemi.com

Features

- Low ON-resistance
- 2.5V drive
- Common-drain type
- Protection diode in
- Built-in gate protection resistor
- Best suited for LiB charging and discharging switch
- Halogen free compliance

Specifications

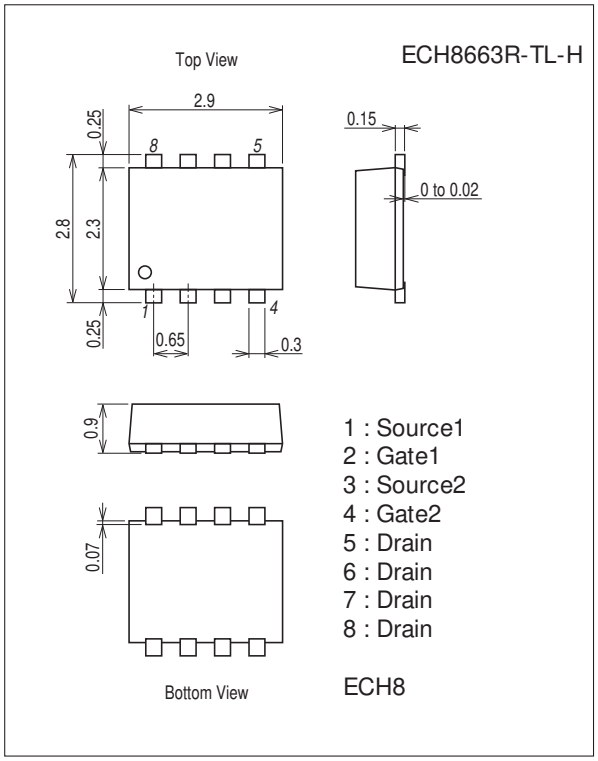
Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSS}		30	V
Gate-to-Source Voltage	V_{GSS}		±12	V
Drain Current (DC)	I_D		8	A
Drain Current (Pulse)	I_{DP}	PW≤10μs, duty cycle≤1%	60	A
Allowable Power Dissipation	P_D	When mounted on ceramic substrate (900mm²×0.8mm) 1unit	1.4	W
Total Power Dissipation	P_T	When mounted on ceramic substrate (900mm²×0.8mm)	1.5	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		−55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Package Dimensions

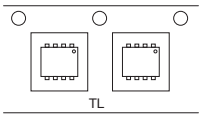
unit : mm (typ)
7011A-003



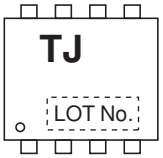
Product & Package Information

- Package : ECH8
- JEITA, JEDEC : -
- Minimum Packing Quantity : 3,000 pcs./reel

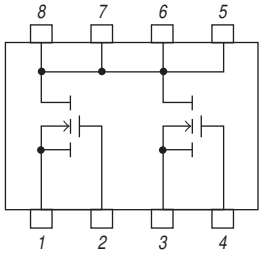
Packing Type : TL



Marking



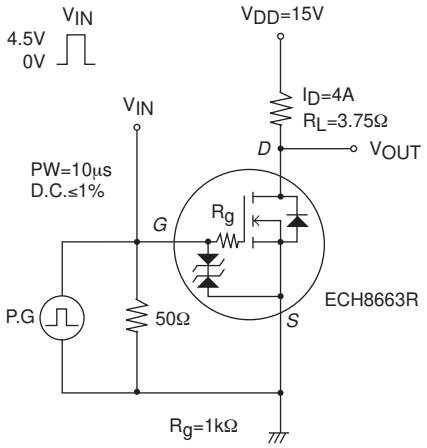
Electrical Connection



Electrical Characteristics at Ta=25°C

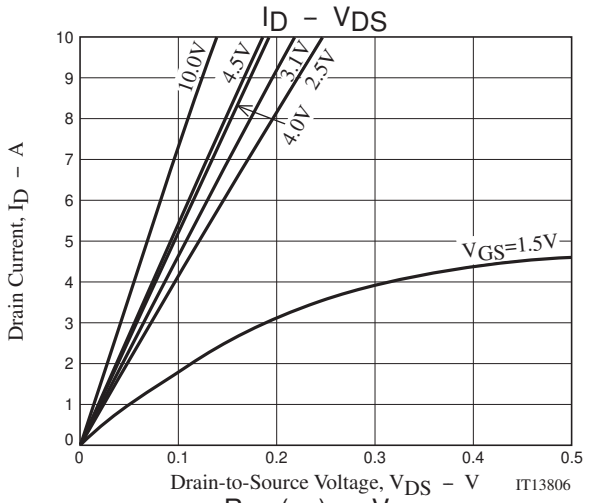
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	I_D=1mA, V_{GS}=0V	30			V
Zero-Gate Voltage Drain Current	I_{DSS}	V_{DS}=30V, V_{GS}=0V			1	μA
Gate-to-Source Leakage Current	I_{GSS}	V_{GS}=±8V, V_{DS}=0V			±10	μA
Cutoff Voltage	V_{GS}(off)	V_{DS}=10V, I_D=1mA	0.5		1.3	V
Forward Transfer Admittance	| yfs |	V_{DS}=10V, I_D=4A	5	8.5		S
Static Drain-to-Source On-State Resistance	R_{DS}(on)1	I_D=4A, V_{GS}=4.5V	10.5	15.5	20.5	mΩ
	R_{DS}(on)2	I_D=4A, V_{GS}=4.0V	11	16	21	mΩ
	R_{DS}(on)3	I_D=2A, V_{GS}=3.1V	12	17.5	23	mΩ
	R_{DS}(on)4	I_D=2A, V_{GS}=2.5V	12	20	28	mΩ
Turn-ON Delay Time	t_d(on)	See specified Test Circuit.		320		ns
Rise Time	t_r			850		ns
Turn-OFF Delay Time	t_d(off)			4200		ns
Fall Time	t_f			1800		ns
Total Gate Charge	Qg	V_{DS}=10V, V_{GS}=4.5V, I_D=8A		12.3		nC
Gate-to-Source Charge	Qgs			2.4		nC
Gate-to-Drain “Miller” Charge	Qgd			2.8		nC
Diode Forward Voltage	V_{SD}	I_S=8A, V_{GS}=0V		0.75	1.2	V

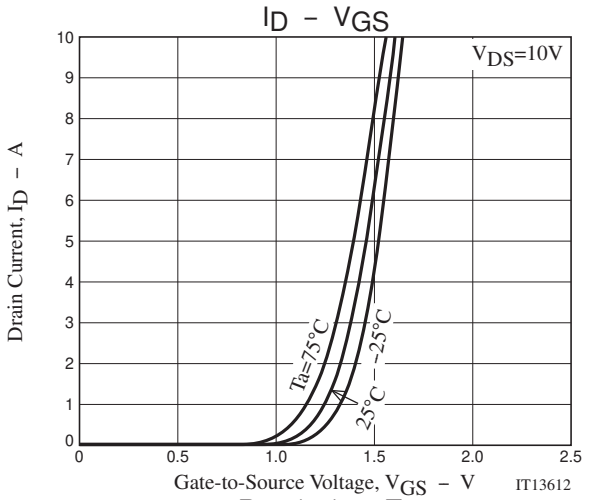
Switching Time Test Circuit

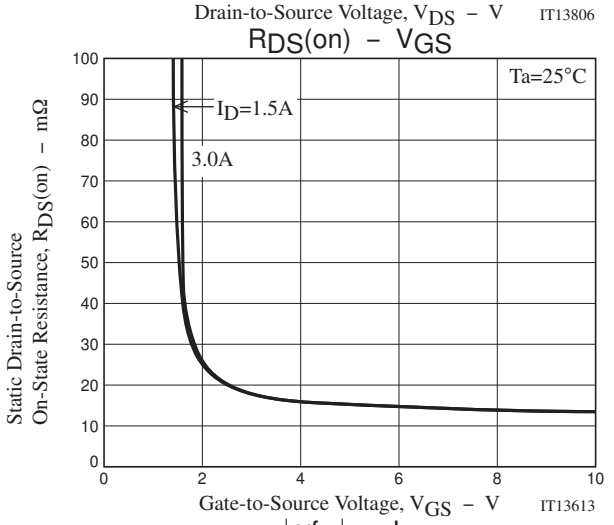


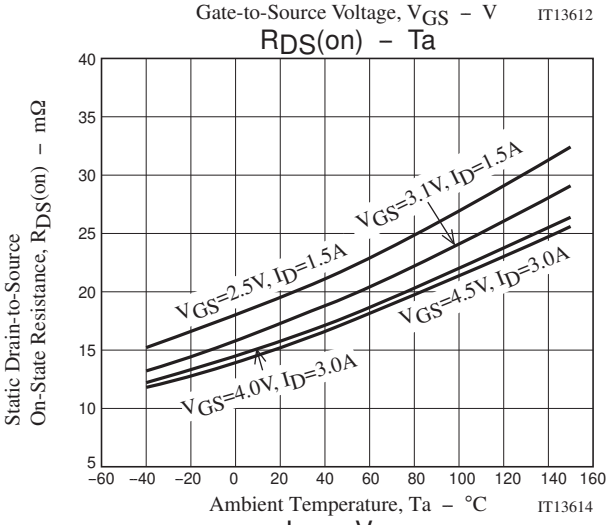
Ordering Information

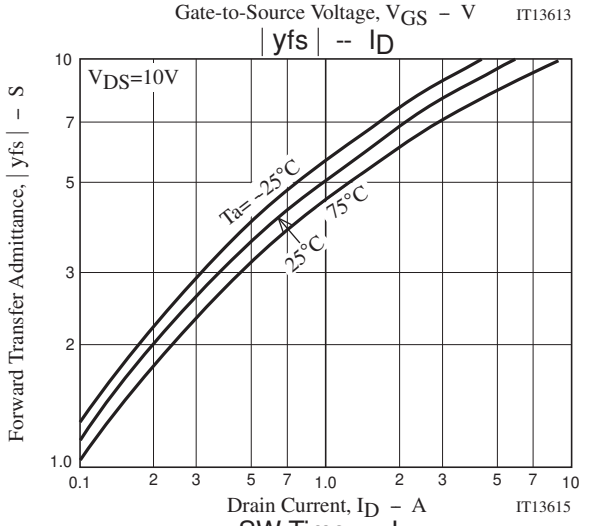
Device	Package	Shipping	memo
ECH8663R-TL-H	ECH8	3,000pcs./reel	Pb Free and Halogen Free

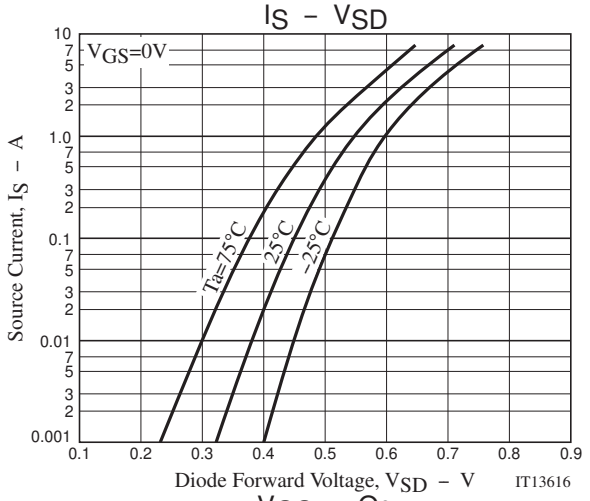

ID – VDS
Drain Current, ID – A
Drain-to-Source Voltage, VDS – V
10.0V
4.5V
3.1V
2.5V
4.0V
VGS=1.5V
IT13806

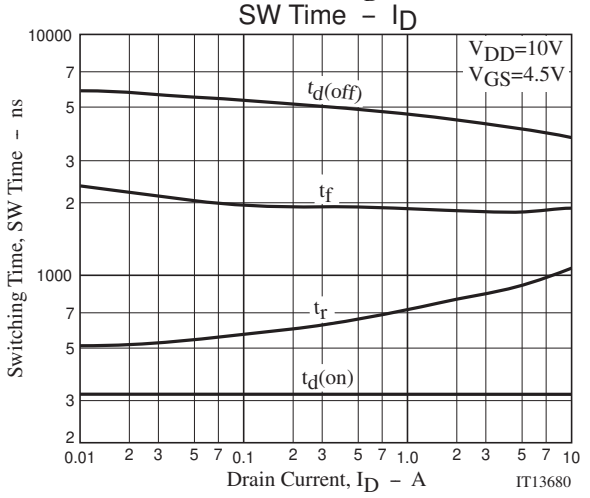

ID – VGS
Drain Current, ID – A
Gate-to-Source Voltage, VGS – V
VDS=10V
Ta=75°C
25°C
–25°C
IT13612

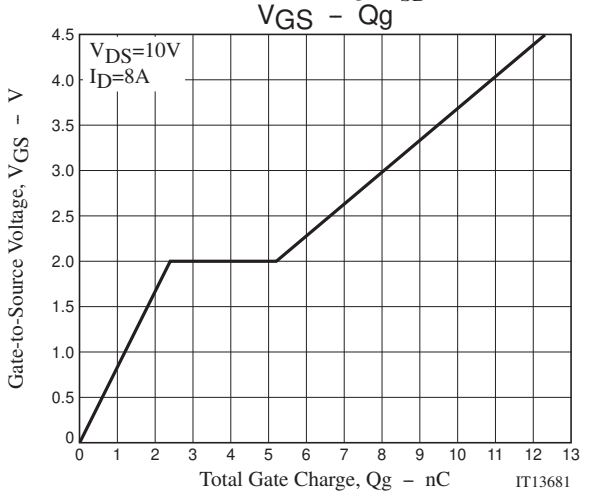

RDS(on) – VGS
Static Drain-to-Source On-State Resistance, RDS(on) – mΩ
Gate-to-Source Voltage, VGS – V
Ta=25°C
ID=1.5A
3.0A
IT13613

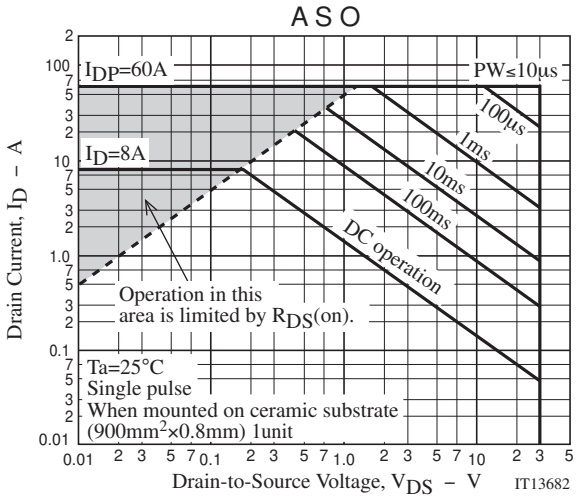

RDS(on) – Ta
Static Drain-to-Source On-State Resistance, RDS(on) – mΩ
Ambient Temperature, Ta – °C
VGS=3.1V, ID=1.5A
VGS=2.5V, ID=1.5A
VGS=4.5V, ID=3.0A
VGS=4.0V, ID=3.0A
IT13614

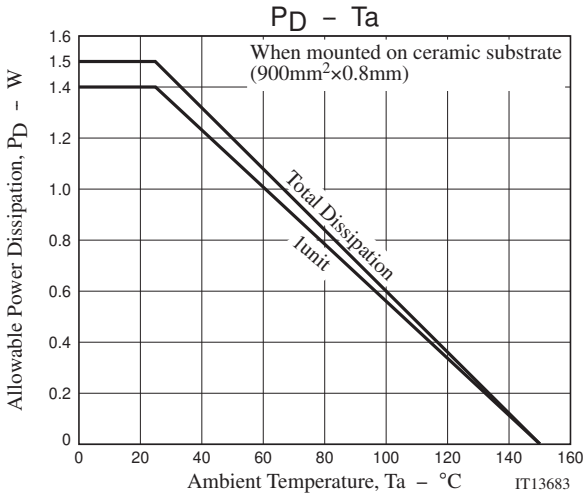

| yfs | -- ID
Forward Transfer Admittance, | yfs | – S
Drain Current, ID – A
VDS=10V
Ta=–25°C
25°C
75°C
IT13615


IS – VSD
Source Current, IS – A
Diode Forward Voltage, VSD – V
VGS=0V
Ta=75°C
25°C
–25°C
IT13616


SW Time – ID
Switching Time, SW Time – ns
Drain Current, ID – A
VDD=10V
VGS=4.5V
td(off)
tf
tr
td(on)
IT13680


VGS – Qg
Gate-to-Source Voltage, VGS – V
Total Gate Charge, Qg – nC
VDS=10V
ID=8A
IT13681


A S O
Drain Current, I_D – A
Drain-to-Source Voltage, V_{DS} – V
I_{DP}=60A
PW≤10μs
I_D=8A
100μs
1ms
10ms
100ms
DC operation
Operation in this
area is limited by R_{DS}(on).
Ta=25°C
Single pulse
When mounted on ceramic substrate
(900mm²×0.8mm) 1unit
IT13682


P_D – Ta
Allowable Power Dissipation, P_D – W
Ambient Temperature, Ta – °C
When mounted on ceramic substrate
(900mm²×0.8mm)
Total Dissipation
1unit
IT13683

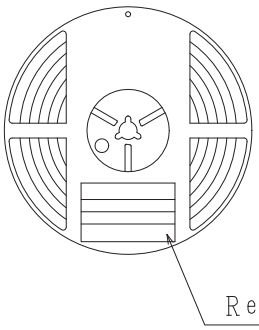
Embossed Taping Specification

ECH8663R-TL-H

1. Packing Format

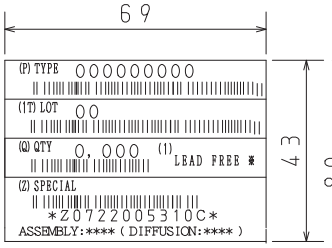
Package Name	Carrier Tape Type	Maximum Number of devices contained (pcs)			Packing format	
		Reel	Inner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)
ECH8	CPH6	3,000	15,000	90,000	5 reels contained Dimensions:mm(external) 183×72×185	6 inner boxes contained Dimensions:mm(external) 440×195×210

Packing method



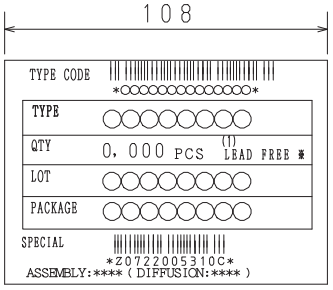
Reel label, Inner box label

(unit:mm)



Outer box label

It is a label at the time of factory shipments. The form of a label may change in physical distribution process.



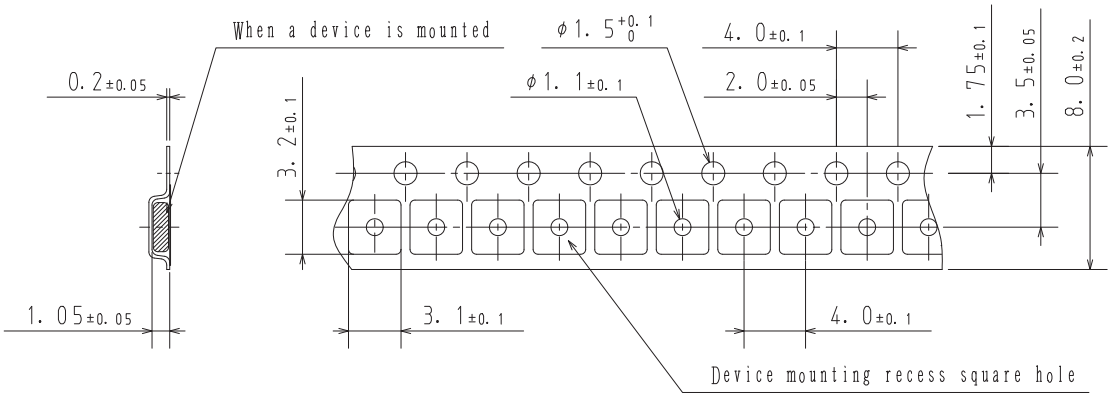
NOTE (1)

The LEAD FREE ※ description shows that the surface treatment of the terminal is lead free.

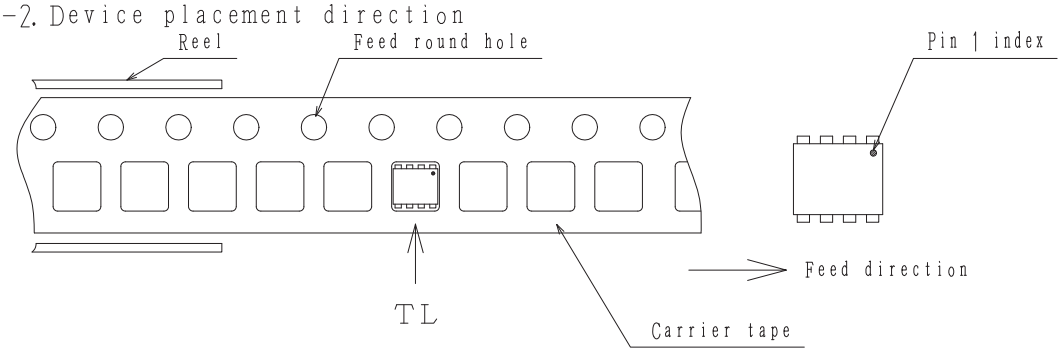
Label	JEITA Phase
LEAD FREE 3	JEITA Phase 3A
LEAD FREE 4	JEITA Phase 3

2. Taping configuration

2-1. Carrier tape size (unit:mm)



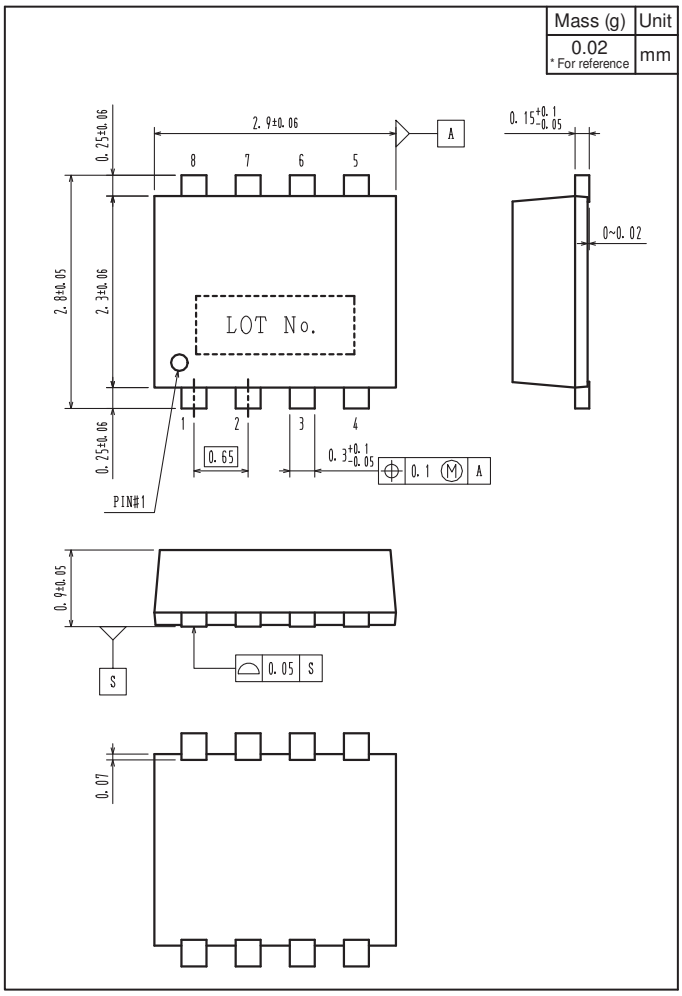
2-2. Device placement direction



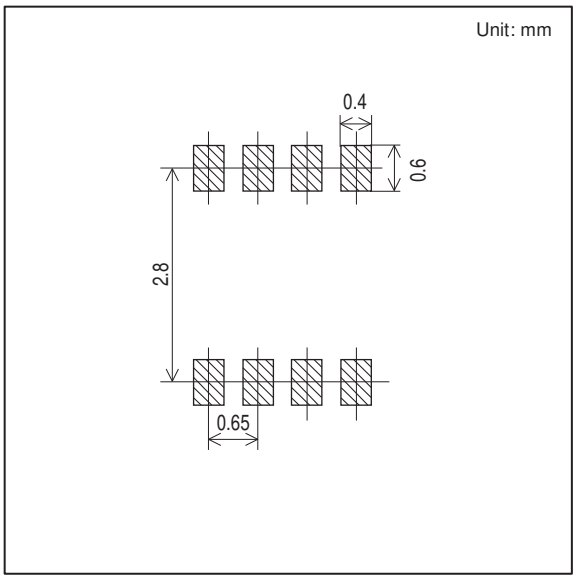
Those with pin 1 index on the feed hole side·····TL

Outline Drawing

ECH8663R-TL-H



Land Pattern Example



Note on usage : Since the ECH8663R is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.